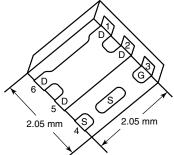


Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)		
- 12	0.029 at V _{GS} = - 4.5 V	- 12 ^a			
	0.034 at V _{GS} = - 2.5 V	- 12 ^a	23 nC		
	0.044 at V _{GS} = - 1.8 V	- 12 ^a	23110		
	0.100 at V _{GS} = - 1.5 V	- 3			

PowerPAK SC-70-6L-Single



FEATURES

- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package - Small Footprint Area
 - Low On-Resistance



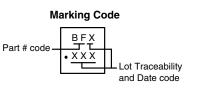
COMPLIANT

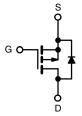
HALOGEN FREE

Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

Load Switch, PA Switch and Battery Switch for Portable Devices





P-Channel MOSFET

Ordering Information: SiA413DJ-T4-GE3 (Lead (Pb)-free and Halogen-free) SiA413DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unle	ess otherwise r	noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 12	V	
Gate-Source Voltage		V _{GS} ± 8		V	
	T _C = 25 °C		- 12 ^a		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	- I _D -	- 12 ^a		
	T _A = 25 °C		- 10 ^{b, c}		
	T _A = 70 °C		- 8 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	- 40		
Continuous Source-Drain Diode Current	T _C = 25 °C	- I _S	- 12 ^a		
	T _A = 25 °C	'S	- 2.9 ^{b, c}		
	T _C = 25 °C		19		
Maximum Power Dissipation	T _C = 70 °C	– P _D	12	w	
	T _A = 25 °C		3.5 ^{b, c}	~~	
	T _A = 70 °C		2.2 ^{b, c}		
Operating Junction and Storage Temperature Ran	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5		

Notes:

a. Package limited.

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b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 80 °C/W.

For more information please contact: pmostechsupport@vishay.com

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					1		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$	- 12			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L _ 250.0A		- 11		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μΑ		2.7			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.4		- 1	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
Zarra Oata Maltana Duria Ormani		$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μA	
Zero Gate Voltage Drain Current	IDSS	V_{DS} = - 12 V, V_{GS} = 0 V, T_{J} = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V_{DS} \leq - 5 V, V_{GS} = - 4.5 V	- 20			Α	
		V _{GS} = - 4.5 V, I _D = - 6.7 A		0.024	0.029	- Ω	
Drain-Source On-State Resistance ^a		$V_{GS} = -2.5 \text{ V}, I_D = -6.2 \text{ A}$		0.028	0.034		
	R _{DS(on)}	V _{GS} = - 1.8 V, I _D = - 2.3 A		0.036	0.044		
		V _{GS} = - 1.5 V, I _D = - 1 A		0.050	0.100		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 6.7 A		30		S	
Dynamic ^b							
Input Capacitance	C _{iss}			1800		pF	
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		450			
Reverse Transfer Capacitance	C _{rss}			390			
-		V _{DS} = - 6 V, V _{GS} = - 8 V, I _D = - 10 A		38	57	-	
Total Gate Charge	Qg			23	35		
Gate-Source Charge	Q_{gs} V _{DS} = - 6 V, V _{GS} = - 4.5 V, I _D = - 10 A Q_{gd}		3		nC		
Gate-Drain Charge				6.5		1	
Gate Resistance	R _g	f = 1 MHz		7		Ω	
Turn-On Delay Time	t _{d(on)}			20	30		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 0.75 Ω		40	60	-	
Turn-Off Delay Time	t _{d(off)}	$\rm I_D \cong$ - 8 A, $\rm V_{GEN}$ = - 4.5 V, $\rm R_g$ = 1 Ω		65	100		
Fall Time	t _f			40	60		
Turn-On Delay Time	t _{d(on)}			10	15	ns	
Rise Time	t _r	V_{DD} = - 6 V, R_L = 0.75 Ω		12	20	1	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 8 A, V_GEN = - 8 V, R_g = 1 Ω		70	105	-	
Fall Time	t _f			40	60		
Drain-Source Body Diode Characterist	cs			•			
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			- 12	۸	
Pulse Diode Forward Current I _{SM}					40	A	
Body Diode Voltage	V _{SD}	I _S = - 8 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time t _{rr}				40	60	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			20	30	nC	
Reverse Recovery Fall Time	t _a	$r_{\rm F} = -6$ A, u/u = 100 A/µs, $r_{\rm J} = 25$ °C		14			
Reverse Recovery Rise Time	t _b			26		ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

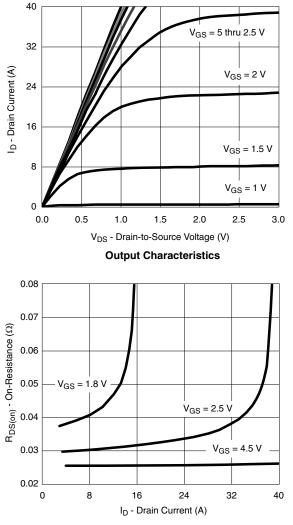
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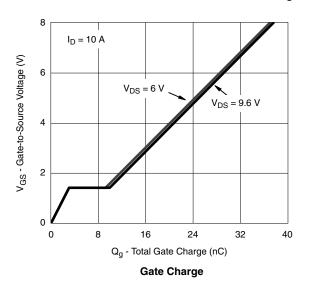


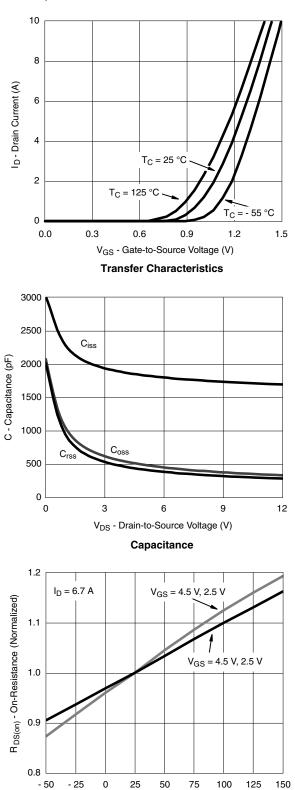
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Drain Current and Gate Voltage





T_J - Junction Temperature (°C) On-Resistance vs. Junction Temperature

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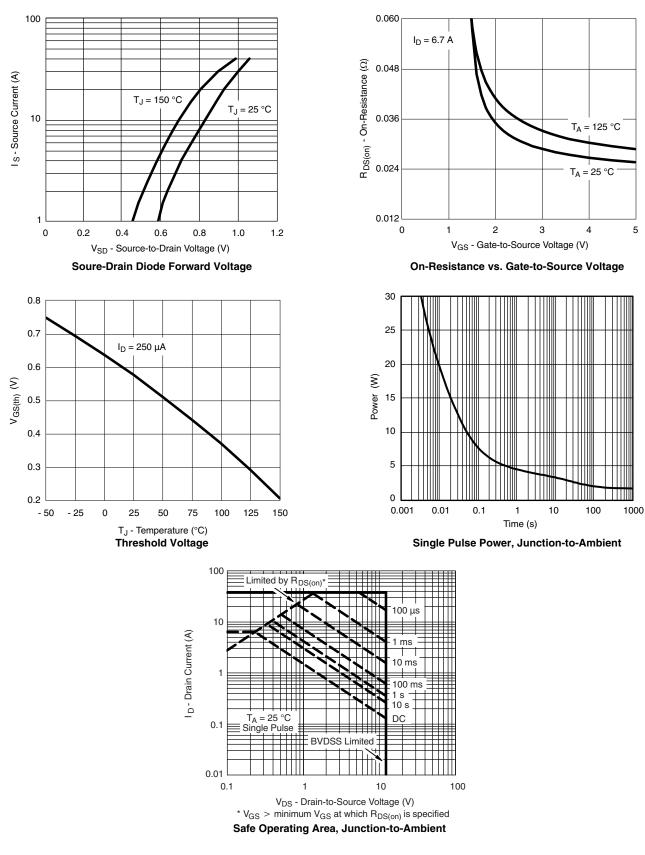
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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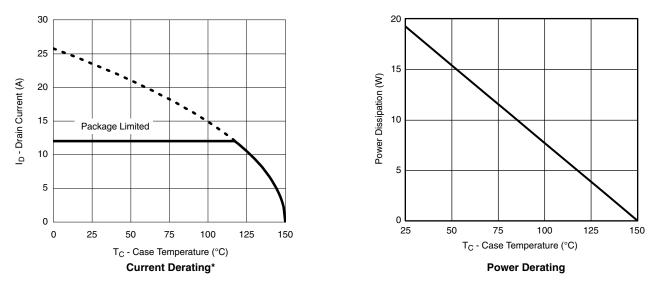
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

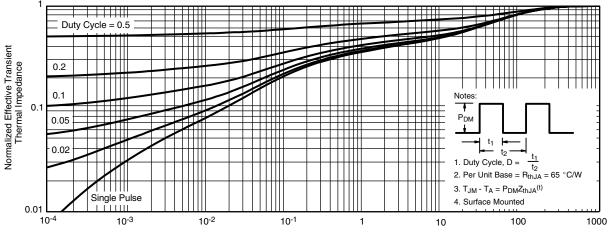


* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

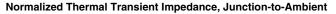


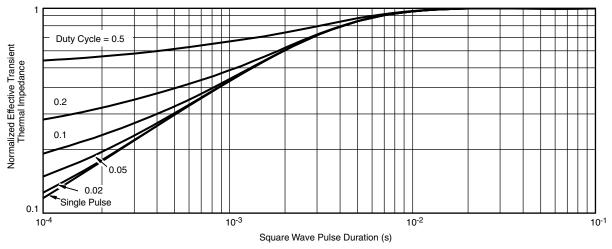
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)





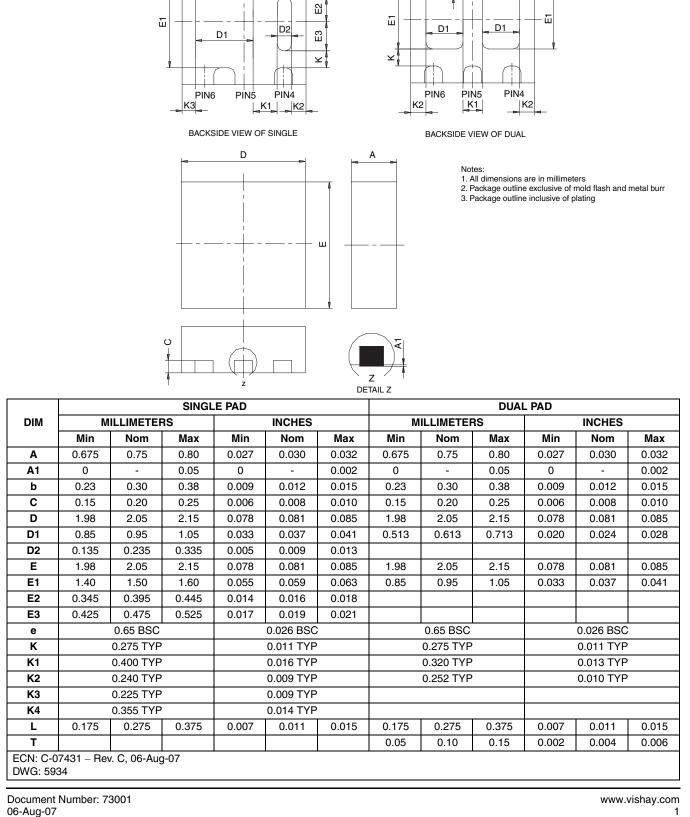
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70447.

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b

PIN3

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PIN2

PIN1

Package Information

b

PIN3

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PIN2

PIN1

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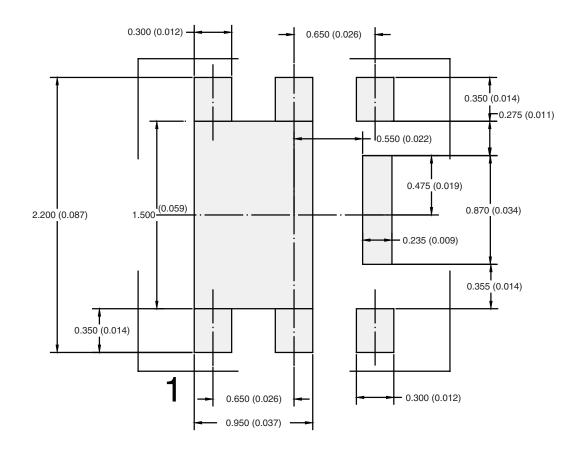
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VISHA

PowerPAK[®] SC70-6L



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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APPLICATION NOTE



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